



DMT3006LFDF

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	$7m\Omega @ V_{GS} = 10V$	14.1A
30V	10mΩ @ V _{GS} = 4.5V	11.8A
	15mΩ @ V_{GS} = 3.7V	9.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- **Battery Management Application**
- **Power Management Functions**
- **DC-DC Converters**

Features

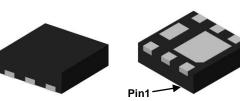
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

N-CHANNEL ENHANCEMENT MODE MOSFET

- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

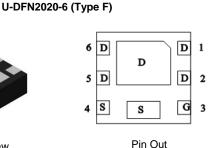
Mechanical Data

- Case: U-DFN2020-6 (Type F) •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0065 grams (Approximate)

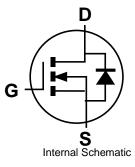


Top View

Bottom View



Bottom View



Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMT3006LFDF-7	7	3,000
DMT3006LFDF-13	13	10,000

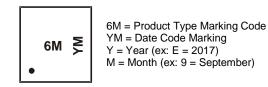
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Date Code Key

Date Obuc hey												
Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E		F	G		Н		
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	ID	14.1 12.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	A
Continuous Source-Drain Diode Current (Note 6)	I _S	2	A
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	25	A
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	31	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	155	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	60	°C/W
Thermal Resistance, Junction to Case (Note 6)	T _C = +25°C	R _{ejc}	6.9	°C/W
Operating and Storage Temperature Range	÷	T _{J.} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

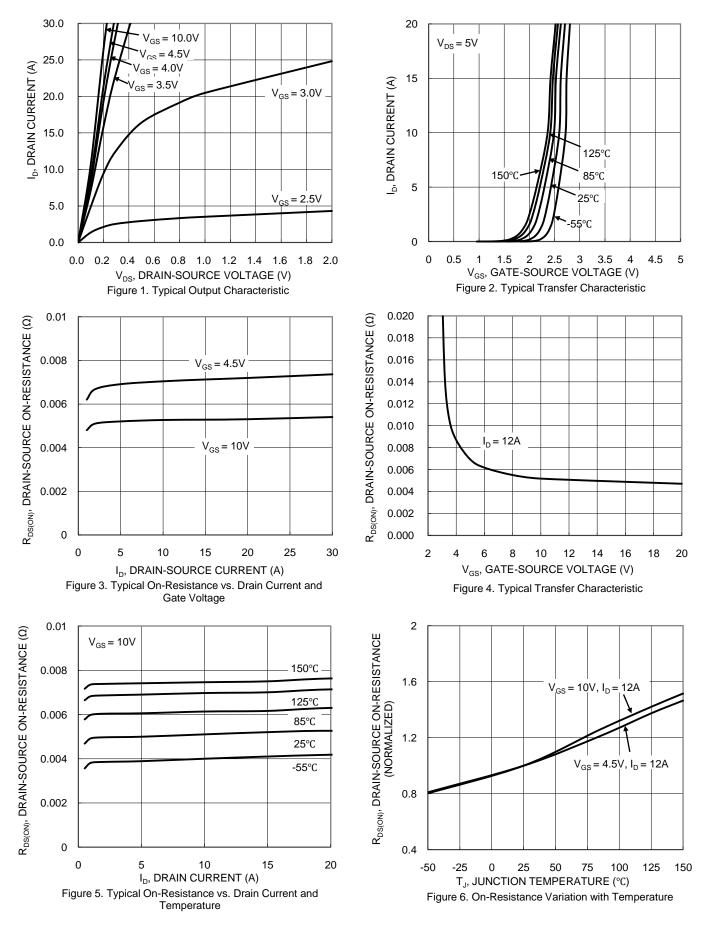
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current (T _J = +25°C)	IDSS	—	_	1	μA	$V_{DS} = 24V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)				•		· · · ·
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			5.8	7		$V_{GS} = 10V, I_D = 9A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	7.8	10	mΩ	$V_{GS} = 4.5V, I_D = 8A$
			9.3	15		$V_{GS} = 3.7V, I_D = 5A$
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 2A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	1,155	-		$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz
Output Capacitance	Coss	_	456	—	pF	
Reverse Transfer Capacitance	C _{rss}	_	72	—		1 = 1.000
Gate Resistance	R _G	_	1.6	-	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	16.7	—		
Total Gate Charge (V _{GS} = 10V)	Q _G	_	8.4	—	-0	
Gate-Source Charge	Q _{GS}	_	2.2	—	nC	$V_{DD} = 15V, I_D = 9A$
Gate-Drain Charge	Q _{GD}	_	3.5	—		
Turn-On Delay Time	t _{D(ON)}	_	3.5	—		
Turn-On Rise Time	t _R	_	5.5	—		$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	13.5	—	ns	$R_G = 3\Omega$, $I_D = 9A$
Turn-Off Fall Time	t _F	_	4.6	—		
Reverse Recovery Time	t _{RR}	_	19.3	—	ns	
Reverse Recovery Charge	Q _{RR}	—	8.6	—	nC	I _F = 1.5A, di/dt = 100A/μs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}$ C. 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.



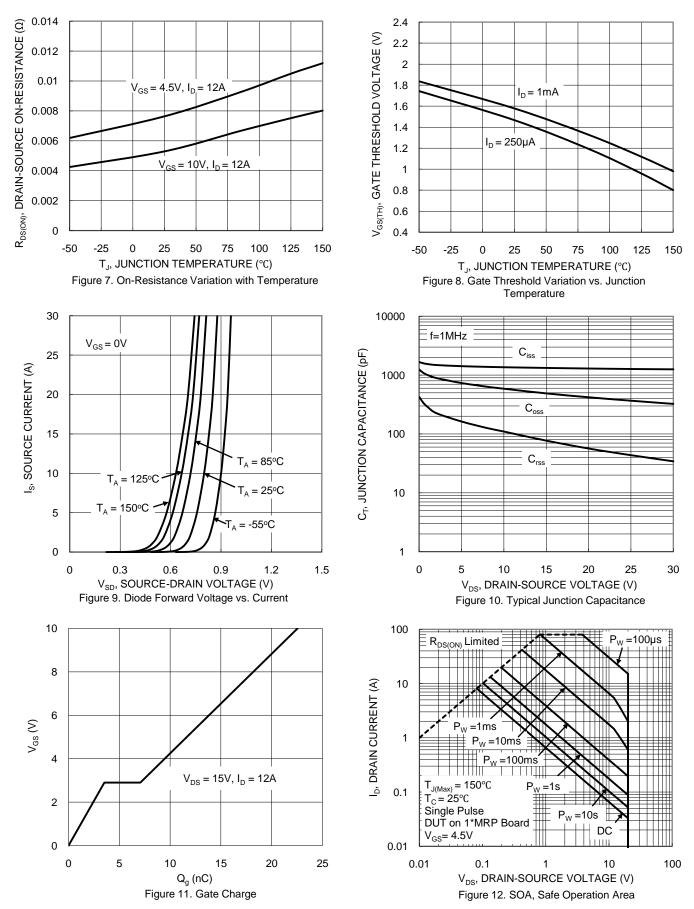
DMT3006LFDF



DMT3006LFDF Datasheet number: DS38250 Rev. 4 - 2 3 of 7 www.diodes.com

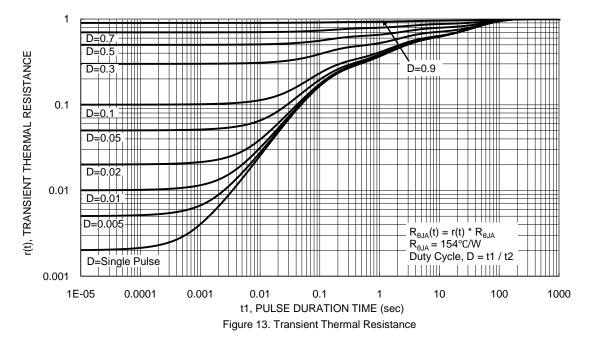


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DMT3006LFDF Datasheet number: DS38250 Rev. 4 - 2



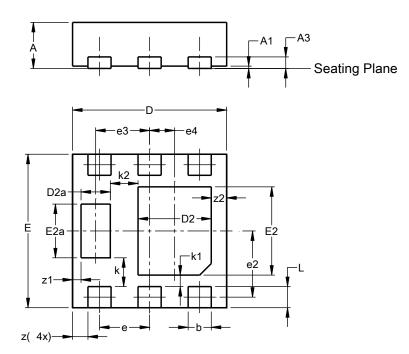




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



U-DFN2020-6									
	(Type F)								
Dim	Min	Max	Тур						
Α	0.57	0.63	0.60						
A1	0.00	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
E	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е	0.65 BSC								
e2	0.863 BSC								
e3		0.70 BSC							
e4	0.325 BSC								
k	0.37 BSC								
k1	0.15 BSC								
k2	0.36 BSC								
L		0.325							
z		0.20 BS							
z1	C).110 BS	SC						
z2		0.20 BS	С						
All C	All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

$Y_{3} Y_{2}$ Pin1 Pin1 Pin2 $Y_{3} Y_{2}$ Y_{4} Y_{7} $Y_{1} Y_{4}$ $Y_{1} Y_{4}$ $Y_{1} Y_{4}$ $Y_{1} Y_{4}$ $Y_{1} Y_{4}$ $Y_{1} Y_{4}$

Dimensions	Value			
Dimensions	(in mm)			
С	0.650			
Х	0.400			
X1	0.480			
X2	0.950 1.700			
X3				
Ý	0.425			
Y1	0.800			
Y2	1.150			
Y3	1.450			
Y4	2.300			

U-DFN2020-6 (Type F)



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